

## Claims

What is claimed is:

1. A method of forming an electrical structure, comprising:
- forming a complex power-signal (CPS) substructure;
  - testing an electrical performance of the CPS substructure to determine whether the CPS substructure satisfies electrical performance acceptance requirements, wherein the testing includes testing for at least one of electrical integrity and electrical signal delay, and wherein the testing for electrical integrity includes testing for at least one of an electrical short, an electrical open, and an erroneous impedance; and
  - if the testing determines that the CPS substructure satisfies the electrical performance acceptance requirements, then forming a dielectric-metallic (DM) laminate on a first external surface of the CPS substructure including forming a first multilevel conductive via through the DM laminate, wherein the DM laminate includes an alternating sequence of an equal number N of dielectric layers and metallic layers such that a first dielectric layer of the N dielectric layers is formed on the first external surface of the CPS substructure, wherein N is at least 2, and wherein the multilevel conductive via is electrically coupled to a first metal layer of the CPS substructure.
2. The method of claim 1, further comprising following the testing: if the testing determines that the CPS substructure does not satisfy the electrical performance acceptance requirements, then forming a new CPS substructure that replaces and thus becomes the CPS substructure and



1 12. The method of claim 1, further comprising forming a conducting via beginning at the first  
2 external surface of the CPS substructure and extending through a fraction of a total thickness of  
3 the CPS substructure, and wherein the first multilevel conductive via is electrically coupled to  
4 the first metal layer of the CPS substructure through the conducting via.

1 13. The method of claim 12, wherein the fraction is less than 1, and wherein the first metal layer  
2 is within an interior of the CPS substructure.

1 14. The method of claim 12, wherein the fraction is less than 1, and wherein the first metal layer  
2 is a complex power-signal of the CPS substructure.

1 15. The method of claim 12, wherein the fraction is equal to 1 such that the conducting via  
2 extends to a second external surface of the CPS substructure, and wherein first metal layer is at  
3 the second external surface.

1 16. The method of claim 1, further comprising coupling a semiconductor chip to a metallic layer  
2 of the N metallic layers that is furthest from the CPS substructure.

1 17. A method of forming an electrical structure, comprising:

2 forming a complex power-signal (CPS) substructure;

3 testing an electrical performance of the CPS substructure to determine whether the CPS  
4 substructure satisfies first electrical performance acceptance requirements, wherein the testing  
5 includes testing for at least one of electrical integrity and electrical signal delay, and wherein the  
6 testing for electrical integrity includes testing for at least one of an electrical short, an electrical  
7 open, and an erroneous impedance; and

8 if the testing determines that the CPS substructure satisfies the first electrical performance  
9 acceptance requirements, then forming a dielectric-metallic (DM) laminate on a first external  
10 surface of the CPS substructure including forming a first multilevel conductive via through the  
11 DM laminate,

12 wherein the DM laminate includes an alternating sequence an equal number of  
13 dielectric layers and metallic layers such that a first dielectric layer of the dielectric layers  
14 is formed on the first external surface of the CPS substructure,

15 wherein the multilevel conductive via is electrically coupled to a first metal layer  
16 of the CPS substructure,

17 wherein after each metallic layer of the metallic layers is formed, examining an  
18 electrical performance of the electrical structure formed thus far to determine whether the  
19 electrical structure satisfies second electrical performance acceptance requirements,

20 wherein the examining includes examining for at least one of an electrical  
21 integrity and electrical signal delay,

22 wherein the examining for electrical integrity includes examining for at least one

of an electrical short, an electrical open, and an erroneous impedance, and  
wherein if the examining determines that the electrical structure satisfies the  
second electrical performance acceptance requirements, then continuing forming the DM  
laminate if less than N metallic layers have been formed else ending forming the DM  
laminate, and  
wherein N is at least 2.

18 . The method of claim 17, further comprising following the testing: if the testing determines  
that the CPS substructure does not satisfy the first electrical performance acceptance  
requirements, then forming a new CPS substructure that replaces and thus becomes the CPS  
substructure and repeating testing an electrical performance of the CPS substructure so replaced.

19 . The method of claim 17, further comprising following the examining: if the examining  
determines that the electrical structure does not satisfy the second electrical performance  
acceptance requirements, then discontinuing forming the DM laminate.

1 20. A method of forming an electrical structure, comprising:  
2 forming a complex power-signal (CPS) substructure;  
3 testing an electrical performance of the CPS substructure to determine whether the CPS  
4 substructure satisfies electrical performance acceptance requirements, wherein the testing  
5 includes testing for at least one of an electrical integrity and electrical signal delay, and wherein  
6 the testing for electrical integrity includes testing for at least one of an electrical short, an  
7 electrical open, and an erroneous impedance; and  
8 if the testing determines that the CPS substructure satisfies the electrical performance  
9 acceptance requirements then:  
10 forming a first dielectric-metallic (DM) laminate on a first external surface of the  
11 CPS substructure including forming a first multilevel conductive via through the first DM  
12 laminate, wherein the first DM laminate includes an alternating sequence of an equal  
13 number N of dielectric layers and metallic layers such that a first dielectric layer of the N  
14 dielectric layers is formed on the first external surface of the CPS substructure, wherein N  
15 is at least 2, and wherein the multilevel conductive via is electrically coupled to a first  
16 metal layer of the CPS substructure, and  
17 forming a second DM laminate on a second external surface of the CPS  
18 substructure including forming a second multilevel conductive via through the second  
19 DM laminate, wherein the second DM laminate includes an alternating sequence of an  
20 equal number M of dielectric layers and metallic layers such that a first dielectric layer of  
21 the M dielectric layers is formed on the second external surface of the CPS substructure,  
22 wherein M is at least 2, and wherein the multilevel conductive via is electrically coupled

23 to a second metal layer of the CPS substructure.

1 21. The method of claim 20, wherein  $M=N$ .

1 22. The method of claim 20, wherein forming the first DM laminate and forming the second DM  
2 laminate comprise forming the first and second DM laminates symmetrically with respect to the  
3 CPS substructure.

1 23. The method of claim 20, further comprising forming a conductive through hole through a  
2 total thickness of the electrical structure, including through the first DM laminate, the CPS  
3 substructure, and the second DM laminate.

1 24. A method of forming an electrical structure, comprising:

2 forming a first complex power-signal (CPS) substructure;

3 testing an electrical performance of the first CPS substructure to determine whether the  
4 first CPS substructure satisfies electrical performance acceptance requirements, wherein the  
5 testing includes testing for at least one of an electrical integrity and electrical signal delay, and  
6 wherein the testing for electrical integrity includes testing for at least one of an electrical short,  
7 an electrical open, and an erroneous impedance;

8 forming a second complex power-signal (CPS) substructure;

9 examining an electrical performance of the second CPS substructure to determine  
10 whether the second CPS substructure satisfies the electrical performance acceptance  
11 requirements, wherein the examining includes examining for at least one of an electrical  
12 integrity and electrical signal delay, and wherein the examining for electrical integrity includes  
13 examining for at least one of an electrical short, an electrical open, and an erroneous impedance;

14 if the testing determines that the first CPS substructure satisfies the electrical performance  
15 acceptance requirements and if the examining determines that the second CPS substructure  
16 satisfies the electrical performance acceptance requirements, then:

17 forming a composite CPS substructure by coupling a first surface of the first CPS  
18 substructure to a first surface of an interfacing dielectric layer and coupling a first surface  
19 of the second CPS substructure to a second surface of the interfacing dielectric layer;

20 forming a first dielectric-metallic (DM) laminate on a second surface of the first  
21 CPS substructure including forming a first multilevel conductive via through the first DM  
22 laminate, wherein the first DM laminate includes an alternating sequence of an equal



number N of dielectric layers and metallic layers such that a first dielectric layer of the N dielectric layers is formed on the second surface of the first CPS substructure, wherein N is at least 2, and wherein the first multilevel conductive via is electrically coupled to a metal layer of the first CPS substructure, and

forming a second DM laminate on a second surface of the second CPS substructure including forming a second multilevel conductive via through the second DM laminate, wherein the second DM laminate includes an alternating sequence of an equal number M of dielectric layers and metallic layers such that a first dielectric layer of the M dielectric layers is formed on the second surface of the second CPS substructure, wherein M is at least 2, and wherein the second multilevel conductive via is electrically coupled to a metal layer of the second CPS substructure.

25. The method of claim 24, wherein  $M=N$ .

26. The method of claim 24, wherein forming the first DM laminate and forming the second DM laminate comprise forming the first and second DM laminates symmetrically with respect to the composite CPS substructure.

27. The method of claim 24, further comprising forming a conductive through hole through a total thickness of the electrical structure, including through the first DM laminate, the composite CPS substructure, and the second DM laminate.

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1 28. An electrical structure, comprising:

2 a complex power-signal (CPS) substructure that has passed an electrical performance

3 acceptance test for at least one of an electrical integrity and electrical signal delay, wherein the

4 test for electrical integrity includes a test for at least one of an electrical short, an electrical open,

5 and an erroneous impedance;

6 a dielectric-metallic (DM) laminate that includes an alternating sequence of an equal

7 number N of dielectric layers and metallic layers such that a first dielectric layer of the N

8 dielectric layers is formed on a first external surface of the CPS substructure, wherein N is at

9 least 2; and

10 a first multilevel conductive via through the DM laminate, wherein the first multilevel

11 conductive via is electrically coupled to a first metal layer of the CPS substructure.

1 29. The electrical structure of claim 28, wherein the first multilevel conductive via is a stacked

2 via.

1 30. The electrical structure of claim 28, wherein the first multilevel conductive via is a deep via.

1 31. The electrical structure of claim 28, wherein the first multilevel conductive via is a simple-

2 deep via

1 32. The electrical structure of claim 28, wherein the first multilevel conductive via is a stacked-

2 deep via.



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1 40. The electrical structure of claim 38, wherein the fraction is less than 1, and wherein the first  
2 metal layer is a complex power-signal of the CPS substructure.

1 41. The electrical structure of claim 38, wherein the fraction is equal to 1 such that the  
2 conducting via extends to a second external surface of the CPS substructure, and wherein first  
3 metal layer is at the second external surface.

1 42. An electrical structure, comprising:

2 a complex power-signal (CPS) substructure that has satisfied an electrical performance  
3 acceptance test for at least one of an electrical integrity and electrical signal delay, and wherein  
4 the test for electrical integrity includes a test for at least one of an electrical short, an electrical  
5 open, and an erroneous impedance;

6 a first dielectric-metallic (DM) laminate that includes an alternating sequence of an equal  
7 number N of dielectric layers and metallic layers such that a first dielectric layer of the N  
8 dielectric layers is formed on a first external surface of the CPS substructure, wherein N is at  
9 least 2, and wherein a first multilevel conductive via through the first DM laminate is electrically  
10 coupled to a first metal layer of the CPS substructure; and

11 a second dielectric-metallic (DM) laminate that includes an alternating sequence of an  
12 equal number M of dielectric layers and metallic layers such that a first dielectric layer of the M  
13 dielectric layers is formed on a second external surface of the CPS substructure, wherein M is at  
14 least 2, and wherein a second multilevel conductive via through the second DM laminate is  
15 electrically coupled to a second metal layer of the CPS substructure.

1 43. The electrical structure of claim 42, wherein  $M=N$ .

1 44. The electrical structure of claim 42, further comprising a conductive through hole through a  
2 total thickness of the electrical structure, including through the first DM laminate, the CPS  
3 substructure, and the second DM laminate.

1 45. An electrical structure, comprising:

2 a composite complex power-signal (CPS) substructure that includes an interfacing  
3 dielectric layer sandwiched between a first CPS substructure and a second CPS substructure,  
4 wherein a first surface of the first CPS substructure is coupled to a first surface of the interfacing  
5 dielectric layer, and wherein a first surface of the second CPS substructure is coupled to a second  
6 surface of the interfacing dielectric layer,

7 said first CPS substructure having passed an electrical performance acceptance  
8 test for at least one of an electrical integrity and electrical signal delay, and wherein the  
9 test for electrical integrity includes a test for at least one of an electrical short, an  
10 electrical open, and an erroneous impedance, and

11 said second CPS substructure having passed the electrical performance acceptance  
12 test for at least one of an electrical integrity and electrical signal delay, and wherein the  
13 test for electrical integrity includes a test for at least one of an electrical short, an  
14 electrical open, and an erroneous impedance,

15 a first dielectric-metallic (DM) laminate that includes an alternating sequence of an equal  
16 number N of dielectric layers and metallic layers such that a first dielectric layer of the N  
17 dielectric layers is formed on a second surface of the first CPS substructure, wherein N is at least  
18 2, and wherein a first multilevel conductive via through the first DM laminate is electrically  
19 coupled to a metal layer of the first CPS substructure; and

20 a second DM laminate that includes an alternating sequence of an equal number M of  
21 dielectric layers and metallic layers such that a first dielectric layer of the M dielectric layers is  
22 formed on a second surface of the second CPS substructure, wherein M is at least 2, and wherein

23 a second multilevel conductive via through the second DM laminate is electrically coupled to a  
24 metal layer of the second CPS substructure.

1 46. The electrical structure of claim 45, wherein  $M=N$ .

1 47. The electrical structure of claim 45, further a conductive through hole through a total  
2 thickness of the electrical structure, including through the first DM laminate, the composite CPS  
3 substructure, and the second DM laminate.

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1 48. An electrical structure, comprising:

2 a complex power-signal (CPS) substructure that has passed an electrical performance  
3 acceptance test for at least one of an electrical integrity and electrical signal delay, and wherein  
4 the test for electrical integrity includes a test for at least one of an electrical short, an electrical  
5 open, and an erroneous impedance;

6 a dielectric-metallic (DM) laminate that includes an alternating sequence of an equal  
7 number N of dielectric layers and metallic layers such that a first dielectric layer of the N  
8 dielectric layers is formed on a first external surface of the CPS substructure, wherein N is at  
9 least 2;

10 a first multilevel conductive via through the DM laminate, wherein the first multilevel  
11 conductive via is electrically coupled to a first metal layer of the CPS substructure; and

12 a semiconductor chip coupled to a metallic layer of the N metallic layers that is furthest  
13 from the CPS substructure.



1 49. An electrical structure, comprising:

2 a complex power-signal (CPS) substructure that has passed an electrical performance  
3 acceptance test for at least one of an electrical integrity and electrical signal delay, and wherein  
4 the test for electrical integrity includes a test for at least one of an electrical short, an electrical  
5 open, and erroneous an impedance;

6 a first dielectric-metallic (DM) laminate that includes an alternating sequence of an equal  
7 number N of dielectric layers and metallic layers such that a first dielectric layer of the N  
8 dielectric layers is formed on a first external surface of the CPS substructure, wherein N is at  
9 least 2, and wherein a first multilevel conductive via through the first DM laminate is electrically  
10 coupled to a first metal layer of the CPS substructure;

11 a second dielectric-metallic (DM) laminate that includes an alternating sequence of an  
12 equal number M of dielectric layers and metallic layers such that a first dielectric layer of the M  
13 dielectric layers is formed on a second external surface of the CPS substructure, wherein M is at  
14 least 2, and wherein a second multilevel conductive via through the second DM laminate is  
15 electrically coupled to a second metal layer of the CPS substructure; and

16 a semiconductor chip coupled to a metallic layer of the N metallic layers that is furthest  
17 from the CPS substructure.

1 50. An electrical structure, comprising:

2 a composite complex power-signal (CPS) substructure that includes an interfacing  
3 dielectric layer sandwiched between a first CPS substructure and a second CPS substructure,  
4 wherein a first surface of the first CPS substructure is coupled to a first surface of the interfacing  
5 dielectric layer, and wherein a first surface of the second CPS substructure is coupled to a second  
6 surface of the interfacing dielectric layer,

7 said first CPS substructure having passed an electrical performance acceptance  
8 test for at least one of an electrical integrity and electrical signal delay, and wherein the  
9 test for electrical integrity includes a test for at least one of an electrical short, electrical  
10 open, and erroneous impedance, and

11 said second CPS substructure having passed the electrical performance acceptance  
12 test for at least one of an electrical integrity and electrical signal delay, and wherein the  
13 test for electrical integrity includes a test for at least one of an electrical short, an  
14 electrical open, and an erroneous impedance,

15 a first dielectric-metallic (DM) laminate that includes an alternating sequence of an equal  
16 number N of dielectric layers and metallic layers such that a first dielectric layer of the N  
17 dielectric layers is formed on a second surface of the first CPS substructure, wherein N is at least  
18 2, and wherein a first multilevel conductive via through the first DM laminate is electrically  
19 coupled to a metal layer of the first CPS substructure;

20 a second DM laminate that includes an alternating sequence of an equal number M of  
21 dielectric layers and metallic layers such that a first dielectric layer of the M dielectric layers is  
22 formed on a second surface of the second CPS substructure, wherein M is at least 2, and wherein

23 a second multilevel conductive via through the second DM laminate is electrically coupled to a  
24 metal layer of the second CPS substructure; and  
25 a semiconductor chip coupled to a metallic layer of the N metallic layers that is furthest  
26 from the first CPS substructure.

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1 51. An electrical structure, comprising  
2 a complex power-signal (CPS) substructure;  
3 a dielectric-metallic (DM) laminate that includes an alternating sequence of an equal  
4 number N of dielectric layers and metallic layers such that a first dielectric layer of the N  
5 dielectric layers is formed on a first external surface of the CPS substructure, wherein N is at  
6 least 2; and  
7 a first multilevel conductive via through the DM laminate, wherein the first multilevel  
8 conductive via is electrically coupled to a first metal layer of the CPS substructure.

1 52. The electrical structure of claim 51, wherein the first multilevel conductive via is a stacked  
2 via.

1 53. The electrical structure of claim 51, wherein the first multilevel conductive via is a deep via.

1 54. The electrical structure of claim 51, wherein the first multilevel conductive via is a simple-  
2 deep via

1 55. The electrical structure of claim 51, wherein the first multilevel conductive via is a stacked-  
2 deep via.

1 56. The electrical structure of claim 51, wherein the CPS substructure is a single CPS  
2 substructure.

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- 1 57. The electrical structure of claim 51, wherein the CPS substructure is a double CPS  
2 substructure.
- 1 58. The electrical structure of claim 51, wherein  $N=2$ .
- 1 59. The electrical structure of claim 51, further comprising a second multilevel conductive via  
2 through the DM laminate, wherein the second multilevel conductive via is electrically coupled to  
3 a second metal layer of the CPS substructure.
- 1 60. The electrical structure of claim 51, wherein the first metal layer is at the first external  
2 surface of the CPS substructure.
- 1 61. The electrical structure of claim 51, further comprising a conducting via beginning at the first  
2 external surface of the CPS substructure and extending through a fraction of a total thickness of  
3 the CPS substructure, and wherein the first multilevel conductive via is electrically coupled to  
4 the first metal layer of the CPS substructure through the conducting via.
- 1 62. The electrical structure of claim 51, wherein the fraction is less than 1, and wherein the first  
2 metal layer is within an interior of the CPS substructure.
- 1 63. The electrical structure of claim 38, wherein the fraction is less than 1, and wherein the first  
2 metal layer is a complex power-signal of the CPS substructure.

1 64. The electrical structure of claim 38, wherein the fraction is equal to 1 such that the  
2 conducting via extends to a second external surface of the CPS substructure, and wherein first  
3 metal layer is at the second external surface.

1 65. The method of claim 38, further comprising a semiconductor chip coupled to a metallic layer  
2 of the N metallic layers that is furthest from the CPS substructure.

FOI b7D b7C b7E b7F b7G b7H b7I b7J b7K b7L b7M b7N b7O b7P b7Q b7R b7S b7T b7U b7V b7W b7X b7Y b7Z